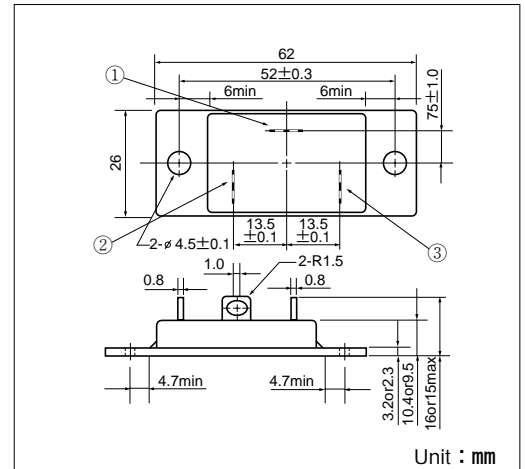
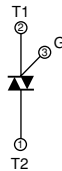


TRIAC (ISOLATED TYPE)

TG70AA40/60

TG70AA40/60 are isolated mould triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light control and heater control.

- $I_{T(AV)}$ 70A
- High surge capability 600A
- Isolated Nounting (AC650V)
- Tab Terminals



Maximum Ratings

(T_j=25°C unless otherwise specified)

Symbol	Item	Ratings		Unit
		TG70AA40	TG70AA60	
V _{DRM}	Repetitive Peak Off-State Voltage	400	600	V
V _{DSM}	Non-Repetitive Peak Off-State Voltage	450	650	V

Symbol	Item	Conditions	Ratings	Unit
I _{T(RMS)}	R.M.S. On-State Current	T _c =58°C	70	A
I _{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	1080/1200	A
I ² t	I ² t		6000	A ² S
P _{GM}	Peak Gate Power Dissipation		10	W
P _{G(AV)}	Average Gate Power Dissipation		1	W
I _{GM}	Peak Gate Current		3	A
V _{GM}	Peak Gate Voltage		10	V
di/dt	Critical Rate of Rise of On-State Current	I _G =100mA, T _j =25°C, V _D =½V _{DRM} , dI _G /dt=1A/μs	50	A/μs
T _j	Operating Junction Temperature		-40 to +125	°C
T _{stg}	Storage Temperature		-40 to +125	°C
V _{iso}	Isolation Breakdown Voltage (R.M.S.)	A.C.1 minute	2500	V
	Mounting Torque (Mounting M4)	Recommended Value 1.0-1.4 (10-14)	1.5 (15)	N·m (kgf·cm)
	Mass			g

Electrical Characteristics

Symbol	Item	Conditions	Ratings			Unit
			Min.	Typ.	Max.	
I _{DRM}	Reptitive Peak Off-State Current	V _D =V _{DRM} , Single phase, half wave, T _j =125°C			10	mA
V _{TM}	Peak On-State Voltage	On-State Current, 100A, I _T =25A, Inst. measurement			1.35	V
I _{GT1} ⁺	Gate Trigger Current	T _j =25°C, I _T =1A, V _D =6V			50	mA
I _{GT1} ⁻		T _j =25°C, I _T =1A, V _D =6V			50	
I _{GT3} ⁺						
I _{GT3} ⁻		T _j =25°C, I _T =1A, V _D =6V			50	
V _{GT1} ⁺	Gate Trigger Voltage	T _j =25°C, I _T =1A, V _D =6V			3	V
V _{GT1} ⁻		T _j =25°C, I _T =1A, V _D =6V			3	
V _{GT3} ⁺						
V _{GT3} ⁻		T _j =25°C, I _T =1A, V _D =6V			3	
V _{GD}	Non-Trigger Gate Voltage	T _j =125°C, V _D =½V _{DRM}	0.2			V
dv/dt	Critical Rate of Rise on-State Voltage,min.	T _j =125°C, V _D =⅔V _{DRM} , Exponential wave.	50			V/μs
[dv/dt] _c	Critical Rate of Rise off-State Voltage at commutation	T _j =125°C, V _D =⅔V _{DRM} , [di/dt] _c =8A/ms	6			V/μs
I _H	Holding Current	T _j =25°C		50	100	mA
R _{th(j-c)}	Thermal Impedance	Junction to case			0.83	°C/W

